2SB1156

Silicon PNP epitaxial planar type

For power switching

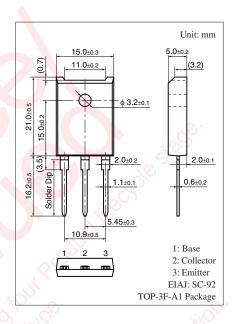
Complementary to 2SD1707

Features

- \bullet Low collector-emitter saturation voltage $V_{\mbox{CE(sat)}}$
- \bullet Satisfactory linearity of forward current transfer ratio h_{FE}
- Large collector current I_C
- Full-pack package which can be installed to the heat sink with one screw

Absolute maximum matings $1^\circ_C = 23^\circ_C$							
Parameter	Symbol Rating		Unit				
Collector-base voltage (Emitter open)	V _{CBO}	-130	V				
Collector-emitter voltage (Base open)	V _{CEO}	-80	V				
Emitter-base voltage (Collector open)	V _{EBO}	-7	V				
Collector current	Ι _C	-20	A				
Peak collector current	I _{CP}	-30	A				
Collector power dissipation	P _C	100	W				
$T_a = 25^{\circ}C$		3					
Junction temperature	Tj	150	°C				
Storage temperature	T _{stg}	-55 to +150	P °C √				





Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = 0$	-80	2		V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -100 \text{ V}, I_E = 0$	- A		-10	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = -5 V, I_C = 0$	2.2		-50	μΑ
Forward current transfer ratio	h _{FE1}	$V_{CE} = -2 V, I_C = -0.1 A$	45			
	h _{FE2} *	$V_{CE} = -2 V, I_C = -3 A$	60		260	
	h _{FE3}	$V_{CE} = -2 V, I_C = -10 A$	30			
Collector-emitter saturation voltage	V _{CE(sat)1}	$I_{\rm C} = -8$ A, $I_{\rm B} = -0.4$ A			- 0.5	V
	V _{CE(sat)2}	$I_{\rm C} = -20$ A, $I_{\rm B} = -2$ A			-1.5	
Base-emitter saturation voltage	V _{BE(sat)1}	$I_{\rm C} = -8$ A, $I_{\rm B} = -0.4$ A			-1.5	V
	V _{BE(sat)2}	$I_{\rm C} = -20$ A, $I_{\rm B} = -2$ A			-2.5	
Transition frequency	f _T	$V_{CE} = -10 \text{ V}, \text{ I}_{C} = -0.5 \text{ A}, \text{ f} = 10 \text{ MHz}$		30		MHz
Turn-on time	t _{on}	$I_{C} = -8 \text{ A}, I_{B1} = -0.8 \text{ A}, I_{B2} = 0.8 \text{ A}$		0.5		μs
Storage time	t _{stg}	$V_{CC} = -50 \text{ V}$		1.0		μs
Fall time	t _f			0.2		μs

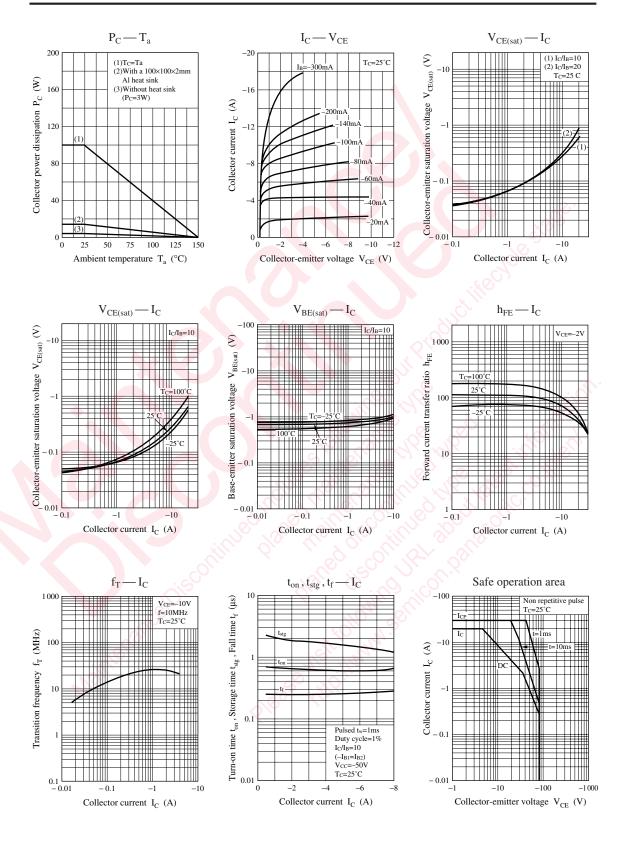
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

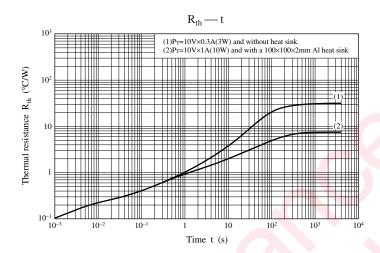
Rank	R	Q	Р
h _{FE2}	60 to 120	90 to 180	130 to 260

Ordering can be made by the common rank (PQ rank $h_{FE2} = 60$ to 240) in the rank classification.

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